Product data sheet

1 General description

The BGU8062 is, also known as the BTS3001M, a high linearity bypass amplifier for wireless infrastructure applications. The BGU8062 is equipped with fast shutdown to support TDD systems. The LNA has a high input and output return loss and is designed to operate between 1.5 GHz and 2.7 GHz. It is housed in a 3 mm × 3 mm × 0.85 mm 10-terminal plastic thin small outline package. The LNA is ESD protected on all terminals.

2 Features and benefits

- Low noise performance: NF = 1.3 dB
- High linearity performance: IP3_O = 36 dBm
- High input return loss > 12 dB
- High output return loss > 15 dB
- · Unconditionally stable up to 20 GHz
- Small 10-terminal leadless package 3 mm × 3 mm × 0.85 mm
- ESD protection on all terminals
- Moisture sensitivity level 1
- Fast shut down to support TDD systems
- +5 V single supply

3 Applications

- · Wireless infrastructure
- Low noise and high linearity applications
- LTE, W-CDMA, CDMA, GSM
- · General-purpose wireless applications
- TDD or FDD systems
- Suitable for small cells



low-noise high-linearity amplifier

4 Quick reference data

Table 1. Quick reference data

f = 1900 MHz; V_{CC} = 5 V; T_{amb} = 25 °C; input and output 50 Ω ; unless otherwise specified. All RF parameters are measured on an application board with the circuit as shown in Figure 29 and components listed in Table 9 implemented. This board is optimized for f = 1900 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CC}	supply current	LNA enable; bypass off	-	70	85	mA
		LNA disable; bypass on	-	3	5	mA
G _{ass}	associated gain	LNA enable; bypass off	17	18.5	20	dB
		LNA disable; bypass on	-2.0	-1.6	-	dB
NF	noise figure	LNA enable; bypass off [1	-	1.3	2.0	dB
P _{L(1dB)}	output power at 1 dB gain compression	LNA enable; bypass off	18.5	20	-	dBm
IP3 _O	output third-order intercept point	2-tone; tone spacing = 1 MHz;P _L = 5 dBm per tone				
		LNA enable; bypass off	33.5	36	-	dBm
		LNA disable; bypass on [2]	40	44	-	dBm

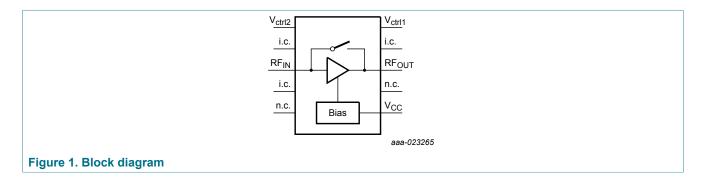
^[1] Connector and Printed-Circuit Board (PCB) losses have been de-embedded.

5 Ordering information

Table 2. Ordering information

Type number	Package		
	Name	Description	Version
BGU8062	HVSON10	plastic thermal enhanced very thin small outline package;no leads; 10 terminals; body $3\times3\times0.85~\text{mm}$	SOT650-2

6 Block diagram

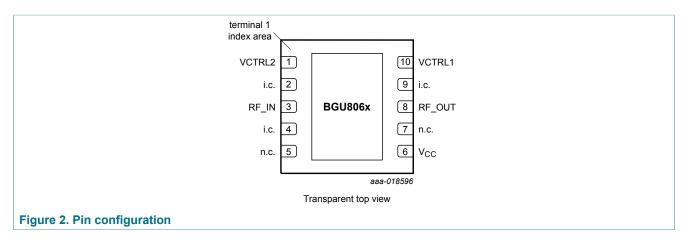


^[2] Guaranteed by device design; not tested in production.

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7 Pinning information

7.1 Pinning



7.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
VCTRL2	1	voltage control 2
i.c.	2, 4, 9	internally connected, can be grounded or left open in the application
RF_IN	3	RF input
n.c.	5	not connected
V _{CC}	6	supply voltage
n.c.	7	not connected
RF_OUT	8	RF output
VCTRL1	10	voltage control 1
GND	exposed die pad	ground

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8 Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). See Section 16.3 "Disclaimers", paragraph "Limiting values".

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-	6	V
V _{I(CTRL1)}	input voltage on pin CTRL1		-	3.6	V
V _{I(CTRL2)}	input voltage on pin CTRL2		-	3.6	V
P _{i(RF)CW}	continuous waveform RF input power		-	20	dBm
T _{stg}	storage temperature		-40	+150	°C
Tj	junction temperature		-	150	°C
Р	power dissipation	$T_{case} \le 125 ^{\circ}C$ [1]	-	510	mW
V _{ESD}	electrostatic discharge voltage	Human Body Model (HBM); according to ANSI/ESDA/JEDEC standard JS-001-2010	-	2.0	kV
		Charged Device Model (CDM); according to JEDEC standard 22-C101B	-	1.0	kV

^[1] Case is ground solder pad.

9 Recommended operating conditions

Table 5. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CC}	supply voltage		4.75	5	5.25	V
Z ₀	characteristic impedance		-	50	-	Ω

10 Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-case)}	thermal resistance from junction to case	[1] [2]	55	K/W

^[1] Case is ground solder pad.

11 Characteristics

Table 7. Characteristics

f = 1900 MHz; V_{CC} = 5 V; T_{amb} = 25 °C; input and output 50 Ω ; unless otherwise specified. All RF parameters are measured on an application board with the circuit as shown in Figure 29 and components listed in Table 9 implemented. This board is optimized for f = 1900 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CC}	supply current	LNA enable; bypass off	-	70	85	mA
		LNA disable; bypass on	-	3	5	mA

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^{2]} Thermal resistance measured using infrared measurement technique, device mounted on application board and placed in still air.

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
G _{ass}	associated gain	LNA enable; bypass off	17	18.5	20	dB
		LNA disable; bypass on	-2.0	-1.6	-	dB
		f = 2600 MHz; LNA enable; bypass off	14	15.5	17	dB
G _{flat}	gain flatness	within 100 MHz bandwidth; LNA enable; bypass off				
		• 1500 MHz ≤ f ≤ 2700 MHz		0.6	-	dB
		• 1900 MHz ≤ f ≤ 2700 MHz	-	0.5	-	dB
NF	noise figure	LNA enable; bypass off	1] -	1.3	2.0	dB
ΔG	gain variation	1900 MHz ≤ f ≤ 2700 MHz	-	3.1	-	dB
P _{L(1dB)}	output power at 1 dB gain compression	LNA enable; bypass off		20	-	dBm
IP3 _O	output third-order intercept point	2-tone; tone spacing = 1 MHz; P _L = 5 dBm per tone				
		LNA enable; bypass off	33.5	36	-	dBm
		LNA disable; bypass on	^{2]} 40	44	-	dBm
RLin	input return loss	LNA enable; bypass off	-	12	-	dB
		LNA disable; bypass on	-	15	-	dB
RLout	output return loss		-	15	-	dB
ISL	isolation	LNA disable; bypass off	20	30	-	dB
		LNA enable; bypass off	15	20	-	dB
t _{s(pon)}	power-on settling time	P _i = -20 dBm	-	8.0	1.0	μs
t _{s(poff)}	power-off settling time	P _i = -20 dBm	-	8.0	1.0	μs
K	Rollett stability factor	both on state and off state up to f = 20 GHz	1	-	-	

^[1] Connector and Printed-Circuit Board (PCB) losses have been de-embedded.

Table 8. Control truth table

 V_{CC} = 5 V; T_{amb} = 25 °C.

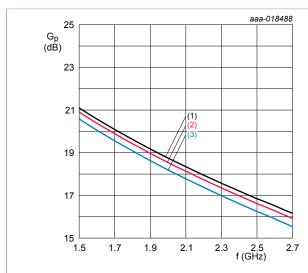
Control signal setting [1]		Mode of operation		
CTRL2 (pin 1)	CTRL1 (pin 10)	LNA	bypass	
HIGH	LOW	disable	on	
HIGH	HIGH	disable	on	
LOW	LOW	enable	off	
LOW	HIGH	disable	off	

^[1] A logic LOW is the result of an input voltage on that specific pin between -0.3 V and +0.7 V. A logic HIGH is the result of an input voltage on that specific pin between 1.2 V and 3.6 V.

^[2] Guaranteed by device design; not tested in production.

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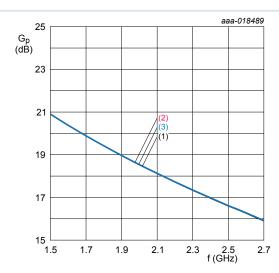
11.1 Graphs



V_{CC}= 5 V; gain mode.

- (1) T_{amb} =-40°C
- (2) $T_{amb} = +25^{\circ}C$
- (3) $T_{amb} = +95^{\circ}C$

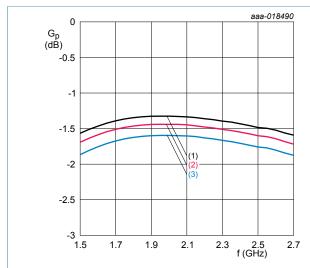
Figure 3. Power gain as a function of frequency; typical values



T_{amb}= 25°C; gain mode.

- (1) V_{CC} = 4.75 V
- (2) V_{CC} = 5.0 V
- $(3) V_{CC} = 5.25 V$

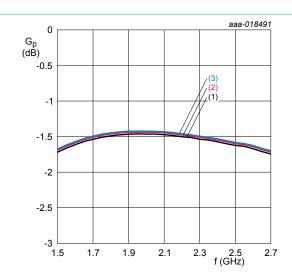
Figure 4. Power gain as a function of frequency; typical values



V_{CC}= 5 V; bypass mode.

- (1) T_{amb}=-40°C
- (2) $T_{amb} = +25^{\circ}C$
- (3) $T_{amb} = +95^{\circ}C$

Figure 5. Power gain as a function of frequency; typical values



T_{amb}= 25°C; bypass mode.

- (1) V_{CC} = 4.75 V
- (2) V_{CC} = 5.0 V
- (3) V_{CC} = 5.25 V

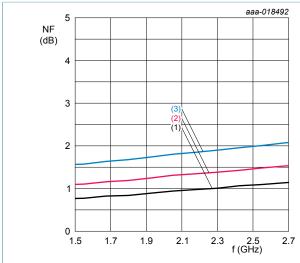
Figure 6. Power gain as a function of frequency; typical values

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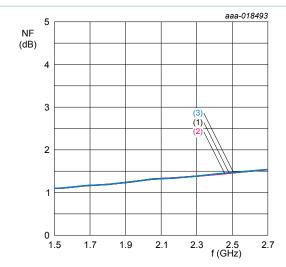
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V_{CC}= 5 V; gain mode.

- (1) T_{amb}=-40°C
- (2) $T_{amb} = +25^{\circ}C$
- (3) $T_{amb} = +95^{\circ}C$

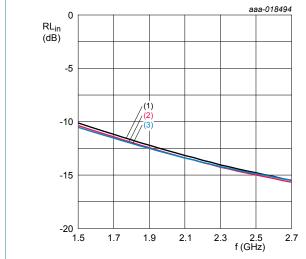
Figure 7. Noise figure as a function of frequency; typical values



T_{amb}= 25°C; gain mode.

- (1) V_{CC} = 4.75 V
- (2) V_{CC} = 5.0 V
- $(3) V_{CC} = 5.25 V$

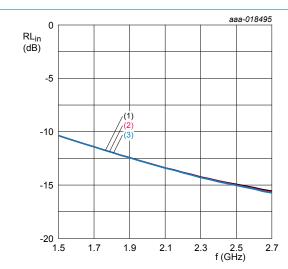
Figure 8. Noise figure as a function of frequency; typical values



V_{CC}= 5 V; gain mode.

- (1) T_{amb}=-40°C
- (2) $T_{amb} = +25^{\circ}C$
- (3) $T_{amb} = +95^{\circ}C$

Figure 9. Input return loss as a function of frequency; typical values

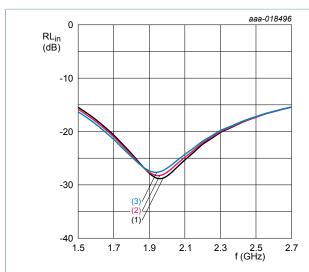


T_{amb}= 25°C; gain mode.

- (1) V_{CC} = 4.75 V
- (2) V_{CC} = 5.0 V
- (3) V_{CC} = 5.25 V

Figure 10. Input return loss as a function of frequency; typical values

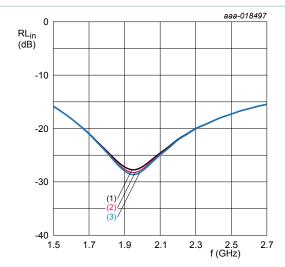
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V_{CC}= 5 V; bypass mode.

- (1) T_{amb}=-40°C
- (2) $T_{amb} = +25^{\circ}C$
- (3) $T_{amb} = +95^{\circ}C$

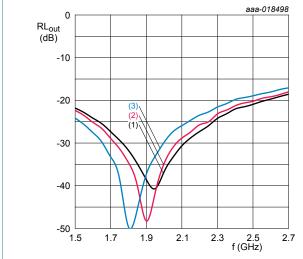
Figure 11. Input return loss as a function of frequency; typical values



T_{amb}= 25°C; bypass mode.

- (1) V_{CC} = 4.75 V
- (2) V_{CC} = 5.0 V
- (3) V_{CC} = 5.25 V

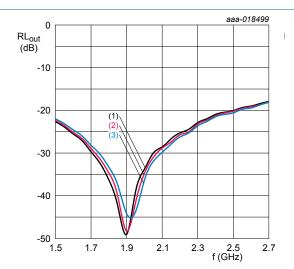
Figure 12. Input return loss as a function of frequency; typical values



V_{CC}= 5 V; gain mode.

- (1) T_{amb}=-40°C
- (2) $T_{amb} = +25^{\circ}C$
- (3) $T_{amb} = +95^{\circ}C$

Figure 13. Output return loss as a function of frequency; typical values

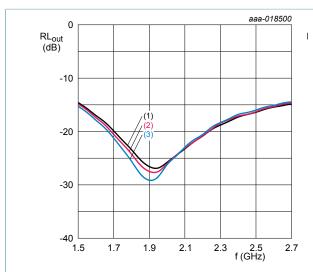


T_{amb}= 25°C; gain mode.

- (1) V_{CC} = 4.75 V
- (2) V_{CC} = 5.0 V
- $(3) V_{CC} = 5.25 V$

Figure 14. Output return loss as a function of frequency; typical values

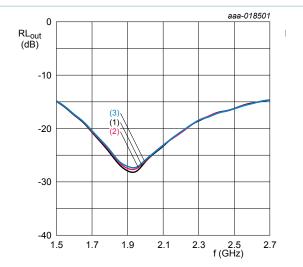
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V_{CC}= 5 V; bypass mode.

- (1) T_{amb}=-40°C
- (2) $T_{amb} = +25^{\circ}C$
- (3) $T_{amb} = +95^{\circ}C$

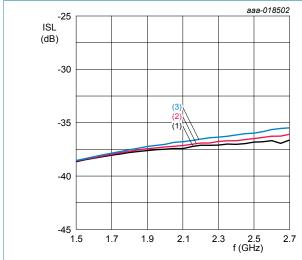
Figure 15. Output return loss as a function of frequency; typical values



T_{amb}= 25°C; bypass mode.

- (1) V_{CC} = 4.75 V
- (2) V_{CC} = 5.0 V
- (3) V_{CC} = 5.25 V

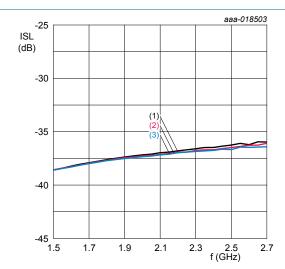
Figure 16. Output return loss as a function of frequency; typical values



V_{CC}= 5 V; isolation mode.

- (1) T_{amb}=-40°C
- (2) $T_{amb} = +25^{\circ}C$
- (3) $T_{amb} = +95^{\circ}C$

Figure 17. Isolation as a function of frequency; typical values

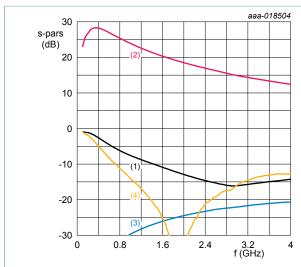


T_{amb}= 25°C; isolation mode.

- (1) V_{CC} = 4.75 V
- (2) V_{CC} = 5.0 V
- $(3) V_{CC} = 5.25 V$

Figure 18. Isolation as a function of frequency; typical values

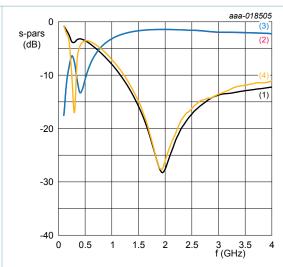
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V_{CC}= 5 V; T_{amb}= 25°C; gain mode.

- $(1) S_{11}$
- (2) S_{21}
- $(3) S_{12}$
- $(4) S_{22}$

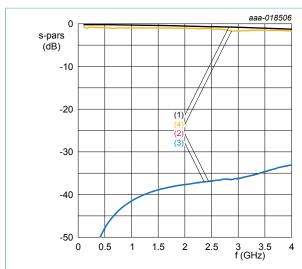
Figure 19. Wideband S-parameters as a function of frequency; typical values



V_{CC}= 5 V; T_{amb}= 25°C; bypass mode.

- $(1) S_{11}$
- $(2) S_{21}$
- $(3) S_{12}$
- $(4) S_{22}$

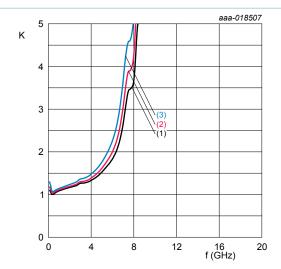
Figure 20. Wideband S-parameters as a function of frequency; typical values



V_{CC}= 5 V; T_{amb}= 25°C; isolation mode.

- $(1) S_{11}$
- $(2) S_{21}$
- $(3) S_{12}$
- $(4) S_{22}$

Figure 21. Wideband S-parameters as a function of frequency; typical values

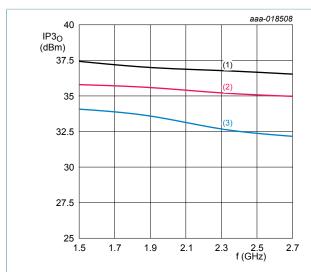


V_{CC}= 5 V; gain mode.

- (1) T_{amb} =-40°C
- (2) $T_{amb} = +25^{\circ}C$
- (3) $T_{amb} = +95^{\circ}C$

Figure 22. Rollett stability factor as a function of frequency; typical values

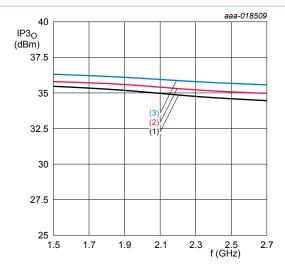
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V_{CC}= 5 V; gain mode.

- (1) T_{amb}=-40°C
- (2) $T_{amb} = +25^{\circ}C$
- (3) $T_{amb} = +95^{\circ}C$

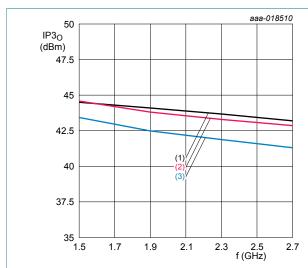
Figure 23. Output third-order intercept point as a function of frequency; typical values



T_{amb}= 25°C; gain mode.

- (1) V_{CC} = 4.75 V
- $(2) V_{CC} = 5.0 V$
- $(3) V_{CC} = 5.25 V$

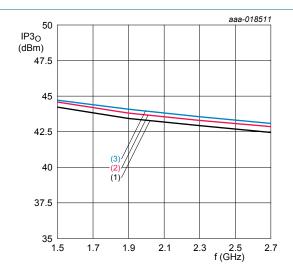
Figure 24. Output third-order intercept point as a function of frequency; typical values



V_{CC}= 5 V; bypass mode.

- (1) T_{amb}=-40°C
- (2) $T_{amb} = +25^{\circ}C$
- (3) $T_{amb} = +95^{\circ}C$

Figure 25. Output third-order intercept point as a function of frequency; typical values

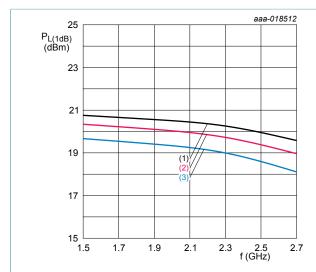


T_{amb}= 25°C; bypass mode.

- (1) $V_{CC} = 4.75 \text{ V}$
- (2) V_{CC} = 5.0 V
- $(3) V_{CC} = 5.25 V$

Figure 26. Output third-order intercept point as a function of frequency; typical values

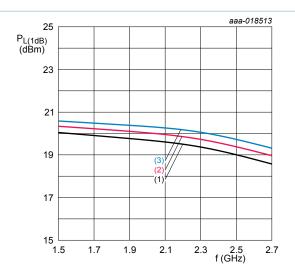
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V_{CC}= 5 V; gain mode.

- (1) T_{amb}=-40°C
- (2) $T_{amb} = +25^{\circ}C$
- (3) $T_{amb} = +95^{\circ}C$

Figure 27. Output power at 1 dB gain compression as a function of frequency; typical values



T_{amb}= 25°C; gain mode.

- (1) V_{CC} = 4.75 V
- (2) V_{CC} = 5.0 V
- $(3) V_{CC} = 5.25 V$

Figure 28. Output power at 1 dB gain compression as a function of frequency; typical values

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12 Application information

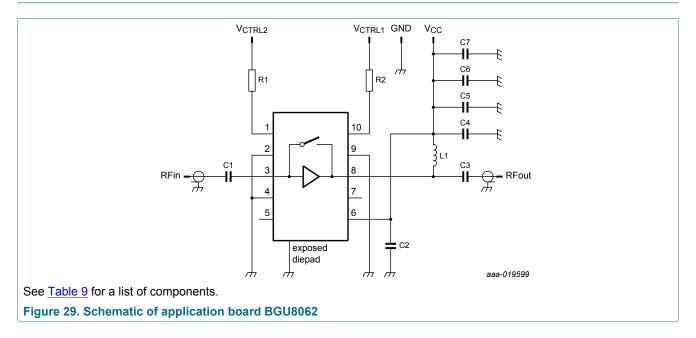


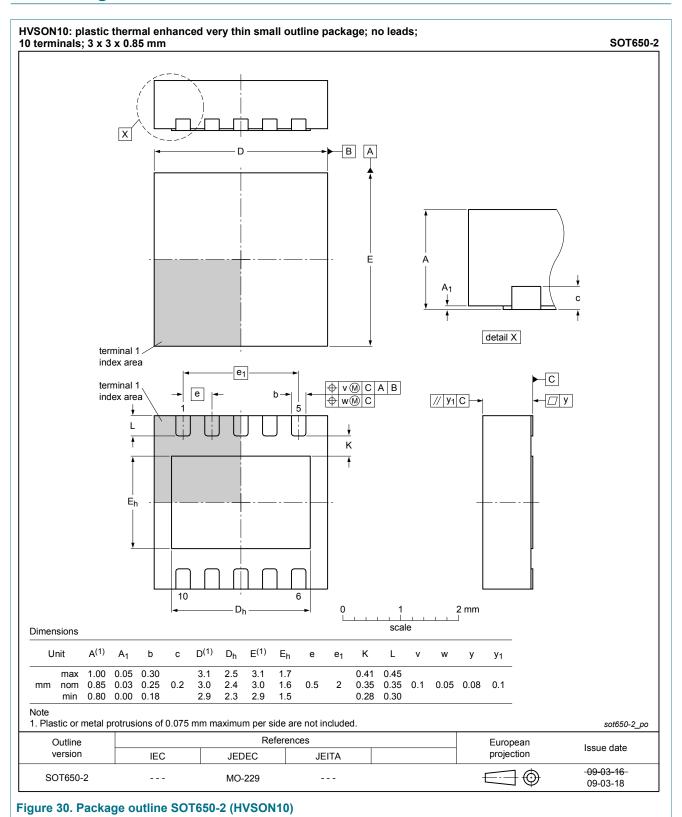
Table 9. List of components

See Figure 29 for schematics.

Component	Description	Value	Remarks
C1	capacitor	100 nF	
C2, C3	capacitor	100 pF	
C4	capacitor	1 nF	
C5	capacitor	-	optional
C6	capacitor	10 nF	
C7	capacitor	1 μF	
L1	inductor	15 nH	
R1, R2	resistor	1 kΩ	

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13 Package outline



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14 Abbreviations

Table 10. Abbreviations

Acronym	Description
CDMA	Code Division Multiple Access
ESD	ElectroStatic Discharge
FDD	Frequency-Division Duplexing
GSM	Global System for Mobile Communication
LNA	Low Noise Amplifier
LTE	Long Term Evolution
TDD	Time-Division Duplexing
W-CDMA	Wideband Code Division Multiple Access

15 Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BGU8062 v.2	20170124	Product data sheet	-	BGU8062 v.1		
Modifications:	 Table 1 added: Min value to IP3_O added BTS3001M according to our new naming convention 					
BGU8062 v.1	20150909	Product data sheet	-	-		

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16 Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- The term 'short data sheet' is explained in section "Definitions". [2] [3]
- The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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low-noise high-linearity amplifier

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